

**Listing of Claims**

1. ( Currently amended) A process comprising:  
~~for depositing an undoped transparent oxide semiconductors~~ semiconductor,  
comprising at least one oxide selected from the group consisting of zinc oxide,  
indium oxide, tin oxide, and cadmium oxide, in a field effect transistor, ~~comprising by~~  
a method selected from the group consisting of :
  - a) physical vapor deposition of an undoped TOS transparent oxide semiconductor in an effective partial pressure of oxygen mixed with an inert gas;
  - b) resistive evaporation of an undoped TOS transparent oxide semiconductor in an effective partial pressure of oxygen;
  - c) laser evaporation of an undoped TOS transparent oxide semiconductor in an effective partial pressure of oxygen;
  - d) electron beam evaporation of an undoped TOS transparent oxide semiconductor in an effective partial pressure of oxygen; and
  - e) chemical vapor deposition of an undoped TOS transparent oxide semiconductor in an effective partial pressure of oxygen.
2. (Currently amended) The process of Claim 1 ~~where~~ wherein the physical vapor deposition is rf magnetron sputtering.
3. (Currently amended) The process of Claim 1 ~~where~~ wherein the physical vapor deposition is dc magnetron sputtering.
4. (Currently amended) The process of Claim 1 ~~where~~ wherein the physical vapor deposition is diode sputtering.
5. (Currently amended) The process of Claim 1 ~~where~~ wherein the physical vapor deposition is triode sputtering.

6. (Currently amended) The process of Claim 1 ~~where~~ wherein the physical vapor deposition is ion beam sputtering.
7. (Original) The process of any of claims 1(a), 2, 3, 4, 5 or 6 wherein deposition is by physical vapor deposition and wherein the inert gas is selected from the group consisting of helium, neon, argon, krypton, and xenon.
8. (Original) The process of Claim 1(e) wherein the chemical vapor deposition is low pressure chemical vapor deposition.
9. (Original) The process of Claim 1(e) wherein the chemical vapor deposition is plasma-enhanced chemical vapor deposition.
10. (Original) The process of Claim 1(e) wherein the chemical vapor deposition is laser-enhanced chemical vapor deposition.
11. (Amended) The process of Claim 1(e) ~~where~~ wherein the chemical vapor deposition is atomic layer chemical vapor deposition.
12. (Original) The process of any one of claims 1 to 11 wherein the effective partial pressure of oxygen is between 0.1 and 10 times the critical pressure.
13. (Original) The process of any one of claims 1 to 11 wherein the effective partial pressure of oxygen is between 0.5 and 2 times the critical pressure.
- 14-24. (Cancelled)